

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (MACH II  $\pi$ -MOS V)

# TPCA8010-H

High-Speed Switching Applications  
 Switching Regulator Applications  
 DC-DC Converter Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge:  $Q_{SW} = 3.7 \text{ nC (typ.)}$
- Low drain-source ON-resistance:  $R_{DS(ON)} = 0.38\Omega \text{ (typ.)}$
- High forward transfer admittance:  $|Y_{fs}| = 3.9S \text{ (typ.)}$
- Low leakage current:  $I_{DSS} = 100 \mu\text{A (max)}$  ( $V_{DS} = 200\text{V}$ )
- Enhancement mode:  $V_{th} = 2.0 \text{ to } 4.0 \text{ V}$  ( $V_{DS} = 10 \text{ V, } I_D = 1 \text{ mA}$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

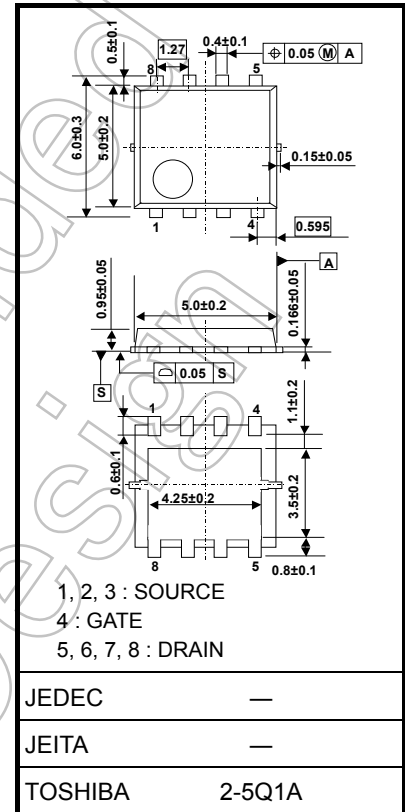
| Characteristic  |                 | Symbol    | Rating     | Unit             |
|---|-----------------|-----------|------------|------------------|
| Drain-source voltage  |                 | $V_{DSS}$ | 200        | V                |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )            |                 | $V_{DGR}$ | 200        | V                |
| Gate-source voltage   |                 | $V_{GSS}$ | $\pm 20$   | V                |
| Drain current   | DC (Note 1)     | $I_D$     | 5.5        | A                |
|   | Pulsed (Note 1) | $I_{DP}$  | 11         |                  |
| Drain power dissipation ( $T_c=25^\circ\text{C}$ )              |                 | $P_D$     | 45         | W                |
| Drain power dissipation ( $t = 10 \text{ s}$ ) (Note 2a)        |                 | $P_D$     | 2.8        | W                |
| Drain power dissipation ( $t = 10 \text{ s}$ ) (Note 2b)        |                 | $P_D$     | 1.6        | W                |
| Single-pulse avalanche energy (Note 3)                          |                 | $E_{AS}$  | 19         | mJ               |
| Avalanche current   |                 | $I_{AR}$  | 5.5        | A                |
| Repetitive avalanche energy ( $T_c=25^\circ\text{C}$ ) (Note 4) |                 | $E_{AR}$  | 1.5        | mJ               |
| Channel temperature   |                 | $T_{ch}$  | 150        | $^\circ\text{C}$ |
| Storage temperature range                                       |                 | $T_{stg}$ | -55 to 150 | $^\circ\text{C}$ |

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

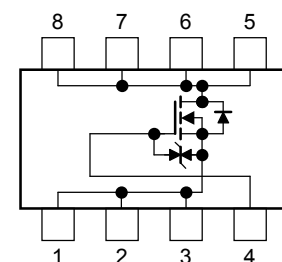
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.069 g (typ.)

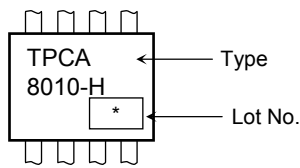
## Circuit Configuration



## Thermal Characteristics

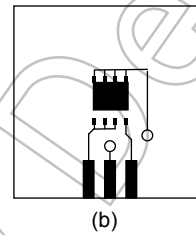
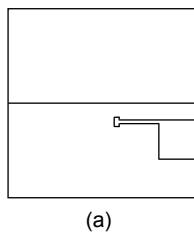
| Characteristic  | Symbol         | Max  | Unit               |
|---|----------------|------|--------------------|
| Thermal resistance, channel to case<br>( $T_c=25^\circ\text{C}$ )         | $R_{th(ch-c)}$ | 2.78 | $^\circ\text{C/W}$ |
| Thermal resistance, channel to ambient<br>( $t = 10\text{ s}$ ) (Note 2a) | $R_{th(ch-a)}$ | 44.6 | $^\circ\text{C/W}$ |
| Thermal resistance, channel to ambient<br>( $t = 10\text{ s}$ ) (Note 2b) | $R_{th(ch-a)}$ | 78.1 | $^\circ\text{C/W}$ |

## Marking (Note 5)



Note 1: The channel temperature should not exceed  $150^\circ\text{C}$  during use.

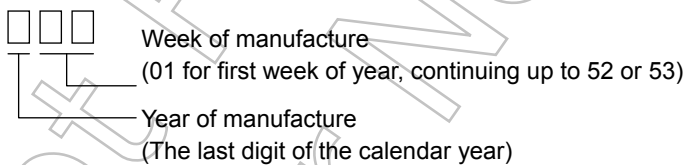
Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



Note 3:  $V_{DD} = 50\text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 1\text{mH}$ ,  $R_G = 25\ \Omega$ ,  $I_{AR} = 5.5\text{ A}$

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: \* Weekly code: (Three digits)

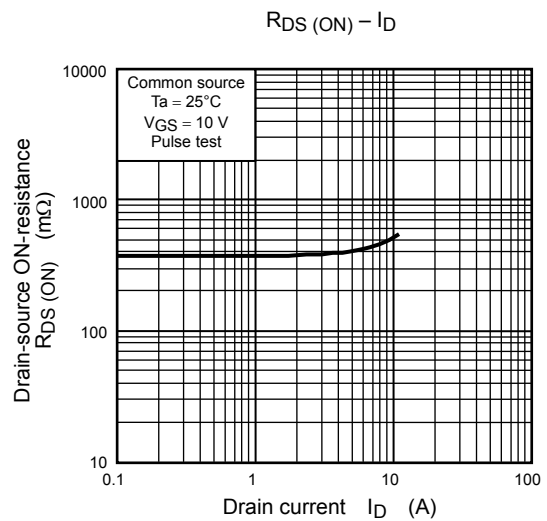
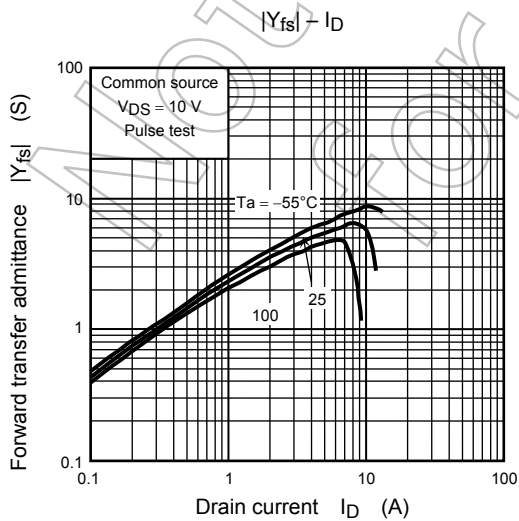
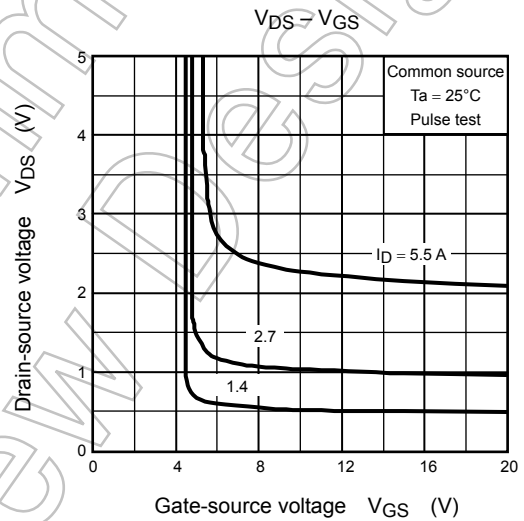
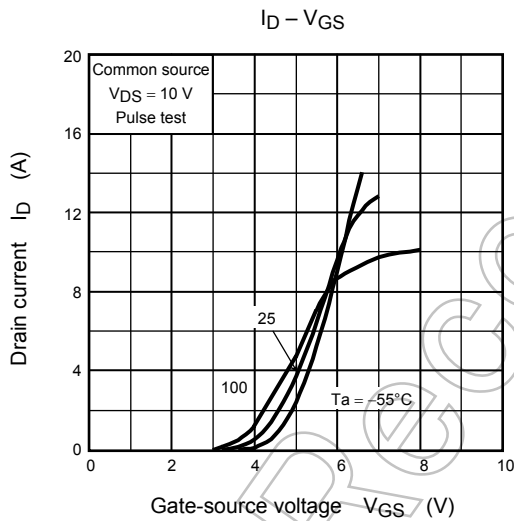
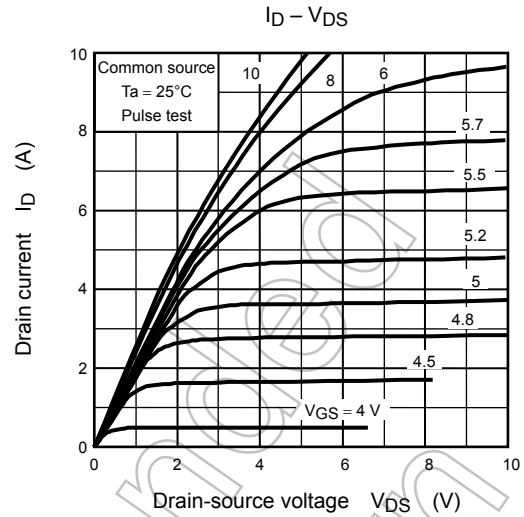
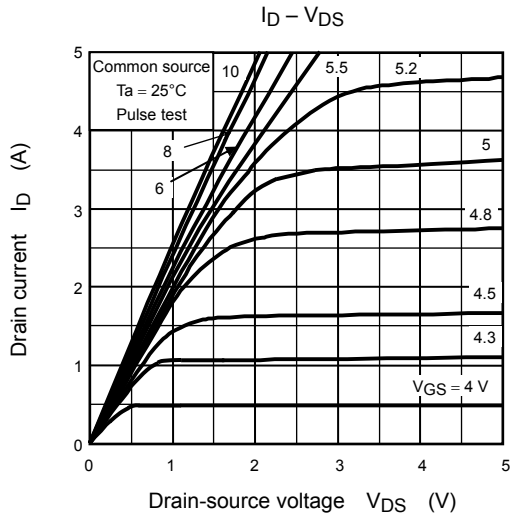


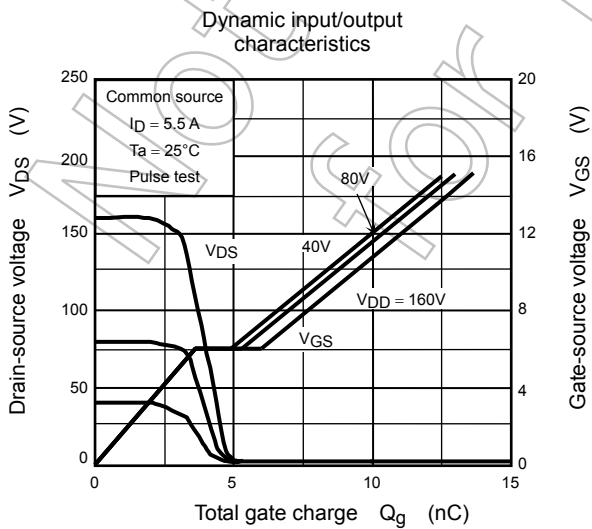
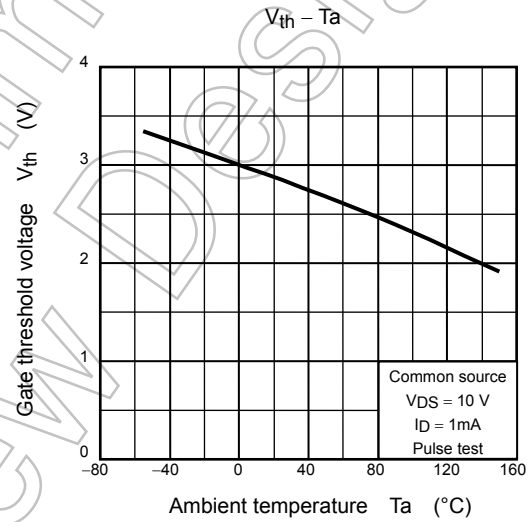
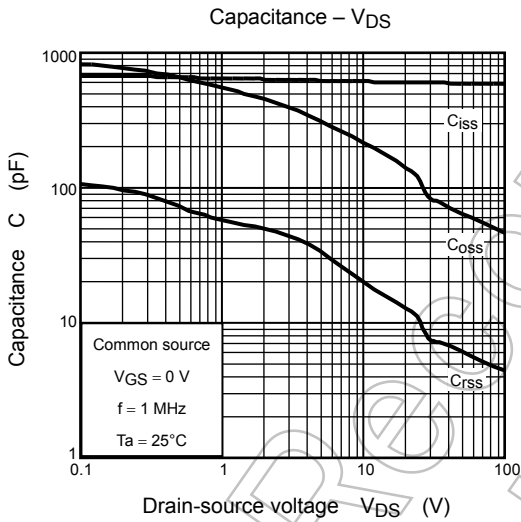
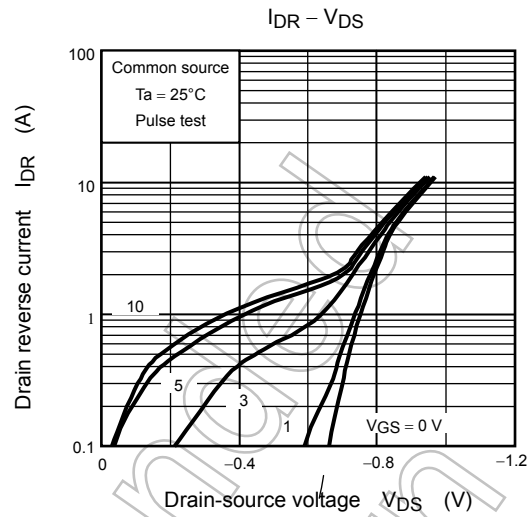
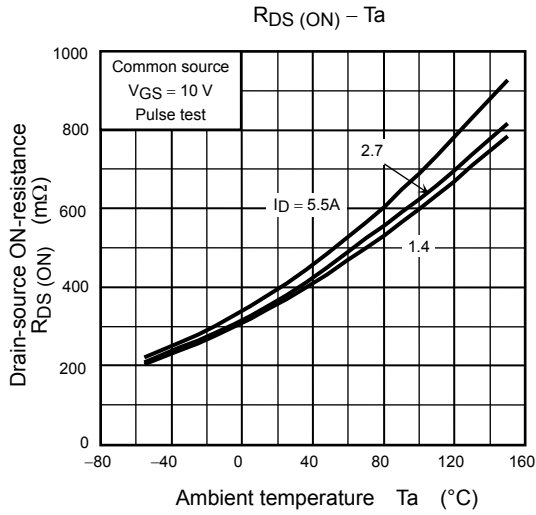
## Electrical Characteristics (Ta = 25°C)

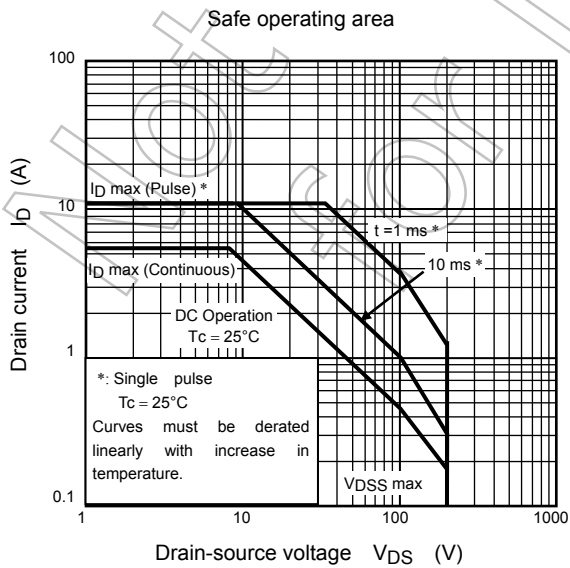
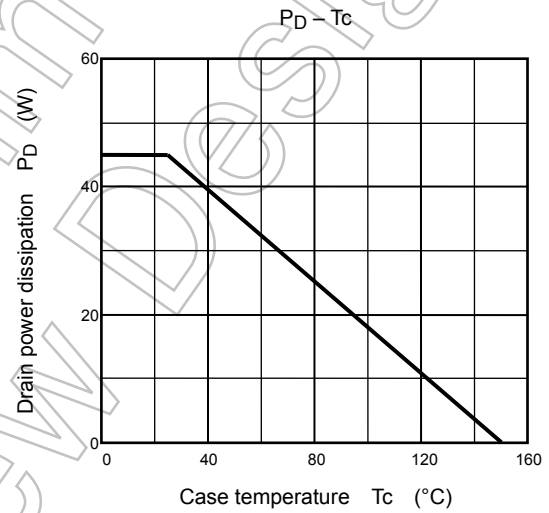
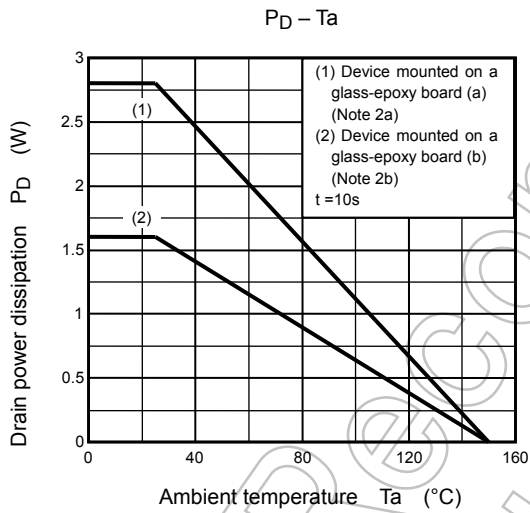
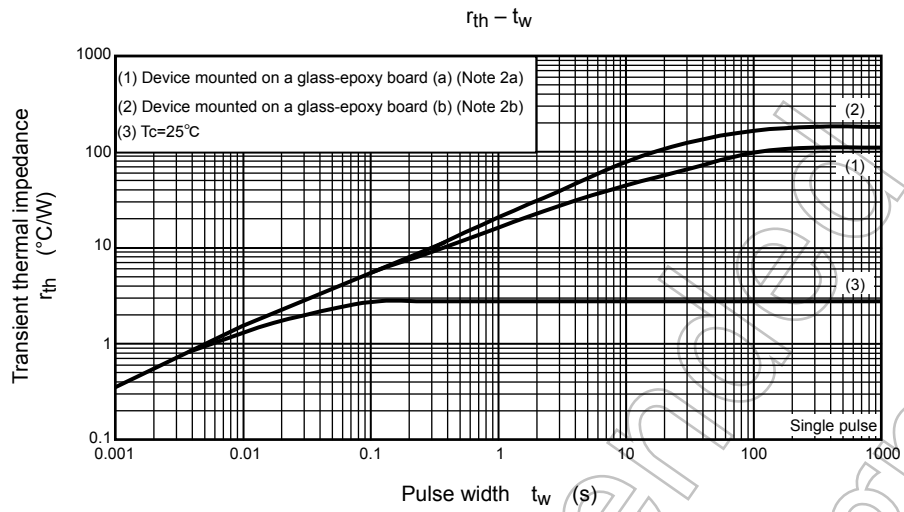
| Characteristic                                  |               | Symbol        | Test Condition  | Min                                       | Typ. | Max      | Unit          |
|---|---------------|---------------|---|---|------|----------|---------------|
| Gate leakage current                            |               | $I_{GSS}$     | $V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$                         | —   | —    | $\pm 10$ | $\mu\text{A}$ |
| Drain cutoff current                            |               | $I_{DSS}$     | $V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$                            | —   | —    | 100      | $\mu\text{A}$ |
| Drain-source breakdown voltage                  |               | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$                               | 200                                       | —    | —        | V             |
|   |               |               | $I_D = 10\text{ mA}, V_{GS} = -5\text{ V}$                              | 200                                       | —    | —        |               |
|   |               | $V_{(BR)DSX}$ | $I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$                             | 150                                       | —    | —        |               |
| Gate threshold voltage                          |               | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$                               | 2.0                                       | —    | 4.0      | V             |
| Drain-source ON-resistance                      |               | $R_{DS(ON)}$  | $V_{GS} = 10\text{ V}, I_D = 2.7\text{ A}$                              | —   | 0.38 | 0.45     | $\Omega$      |
| Forward transfer admittance                     |               | $ Y_{fs} $    | $V_{DS} = 10\text{ V}, I_D = 2.7\text{ A}$                              | 1.8                                       | 3.9  | —        | S             |
| Input capacitance                               |               | $C_{iss}$     | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$           | —   | 600  | —        | pF            |
| Reverse transfer capacitance                    |               | $C_{rss}$     |   | —   | 20   | —        |               |
| Output capacitance                              |               | $C_{oss}$     |   | —   | 220  | —        |               |
| Switching time                                  | Rise time     | $t_r$         |   | —   | 8    | —        | ns            |
|   | Turn-ON time  | $t_{on}$      |   | —   | 17   | —        |               |
|   | Fall time     | $t_f$         |   | —   | 13   | —        |               |
|   | Turn-OFF time | $t_{off}$     |   | Duty $\leq 1\%$ , $t_w = 10\ \mu\text{s}$ | —    | 70       |               |
| Total gate charge (gate-source plus gate-drain) |               | $Q_g$         | $V_{DD} \approx 160\text{ V}, V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}$ | —   | 10   | —        | nC            |
| Gate-source charge                              |               | $Q_{gs}$      |   | —   | 7.6  | —        |               |
| Gate-drain ("miller") charge                    |               | $Q_{gd}$      |   | —   | 2.4  | —        |               |
| Gate switch charge                              |               | $Q_{sw}$      |   | —   | 3.7  | —        |               |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristic          |                | Symbol    | Test Condition                               | Min | Typ. | Max  | Unit |
|-------------------------|----------------|-----------|--|-----|------|------|------|
| Drain reverse current   | Pulse (Note 1) | $I_{DRP}$ | —  | —   | —    | 11   | A    |
| Forward voltage (diode) |                | $V_{DSF}$ | $I_{DR} = 5.5\text{ A}, V_{GS} = 0\text{ V}$ | —   | —    | -2.0 | V    |







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